Vishay Semiconductors

Hyperfast Rectifier, 30 A FRED Pt[®] G5



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LINKS TO ADDITIONAL RESOURCES



PRIMARY CHARACTERISTICS						
I _{F(AV)} 30 A						
V _R	600 V					
V _F at I _F at 125 °C	1.3 V					
t _{rr} (typ.)	22					
I _{FSM}	310					
T _J max.	175 °C					
Package	TO-247AD 2L					
Circuit configuration Single						

FEATURES

- Hyperfast and optimized Q_{rr}
- · Best in class forward voltage drop and switching losses trade off
- Optimized for high speed operation
- 175 °C maximum operating junction temperature FREE
- · Polyimide passivation
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

DESCRIPTION / APPLICATIONS

Featuring a unique combination of low conduction and switching losses, this rectifier is the right choice for soft switched and resonant converters, as well as medium frequency hard switching converters. This device is specifically designed to improve efficiency of high speed LLC output rectification stages of EV / HEV battery charging stations and high frequency stages of UPS applications.

MECHANICAL DATA

Case: TO-247AD 2L Molding compound meets UL 94 V-0 flammability rating Terminal: matte tin plated leads, solderable per J-STD-002

ABSOLUTE MAXIMUM RATINGS					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Repetitive peak reverse voltage	V _{RRM}		600	V	
Average rectified forward current	I _{F(AV)}	T _C = 117 °C, D = 0.50	30		
Non-repetitive peak surge current	I _{FSM}	T_{C} = 25 °C, t_{p} = 10 ms, sine wave both anodes, (1) and (3) connected	310	А	
Repetitive peak forward current	I _{FRM}	T _C = 117 °C, D = 0.50, f = 20 kHz	60		
Operating junction and storage temperature	T _J , T _{Stg}		-55 to +175	°C	

ELECTRICAL SPECIFICATIONS ($T_J = 25 \text{ °C}$ unless otherwise specified)						
PARAMETER	SYMBOL	. TEST CONDITIONS MIN. TYP.		MAX.	UNITS	
Breakdown voltage, blocking voltage	V _{BR} ,V _R	I _R = 100 μA	600	-	-	
Forward voltage	V _F	I _F = 30 A	-	1.6	2.1	V
		I _F = 30 A, T _J = 125 °C	-	1.3	-	
Reverse leakage current	I _R	V _R = V _R rated	-	-	20	
		$T_J = 125 \text{ °C}, V_R = V_R \text{ rated}$	-	-	500	μA
Junction capacitance	CT	V _R = 200 V	-	36	-	pF
Series inductance	L _S	Measured to lead 5 mm from package body	-	8	-	nH

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VS-E5PX3006L-N3



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DYNAMIC RECOVERY CHARACTERISTICS ($T_J = 25$ °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
		$I_F = 1.0 \text{ A}, \text{ d}I_F/\text{d}t = 100 \text{ A}/\mu\text{s}, \text{ V}_R = 30 \text{ V}$		-	22	-	
Reverse recovery time	t _{rr}	T _J = 25 °C		-	39	-	ns
		T _J = 125 °C		-	50	-	
Book rocovery ourrent	1	T _J = 25 °C	I _F = 20 A dI _F /dt = 1000 A/μs V _R = 400 V	-	14	-	A
Peak recovery current	I _{RRM}	T _J = 125 °C		-	24	-	
	0	T _J = 25 °C		-	253	-	
Reverse recovery charge	Q _{rr}	T _J = 125 °C		-	785	-	nC
		T _J = 25 °C	I _F = 30 A dI _F /dt = 1000 A/μs V _R = 400 V	-	41	-	
Reverse recovery time	t _{rr}	T _J = 125 °C		-	56	-	ns
Peak recovery current	I _{RRM}	T _J = 25 °C		-	16	-	A
		T _J = 125 °C		-	27	-	
Reverse recovery charge		T _J = 25 °C		-	306	-	nC
	Q _{rr}	T _J = 125 °C		-	952	-	

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Thermal resistance, junction-to-case	R _{thJC}		-	-	1.1	°C/W
Weight			-	5.5	-	g
			-	0.2	-	oz.
Mounting torque			6 (5)	-	12 (10)	kgf · cm (lbf · in)
Maximum junction and storage temperature range	T _J , T _{Stg}		-55	-	175	°C
Marking device		Case style: TO-247AD 2L	E5PX3006L			

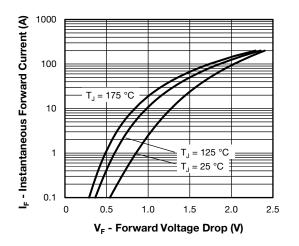


Fig. 1 - Typical Forward Voltage Drop Characteristics

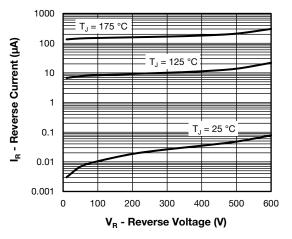
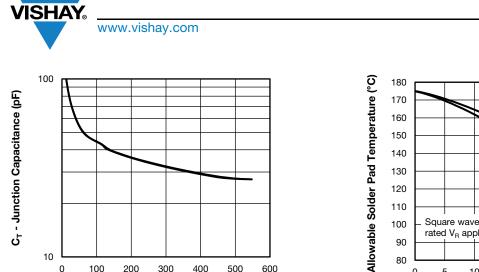


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

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80 600 400 500 V_R - Reverse Voltage (V)

Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

300

10

0

100

200

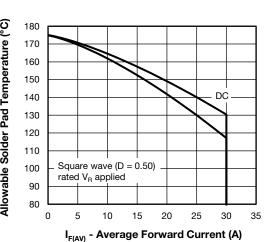


Fig. 4 - Maximum Allowable Case Temperature vs. Average Forward Current

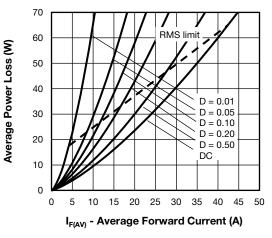


Fig. 5 - Average Power Loss vs. Average Forward Current

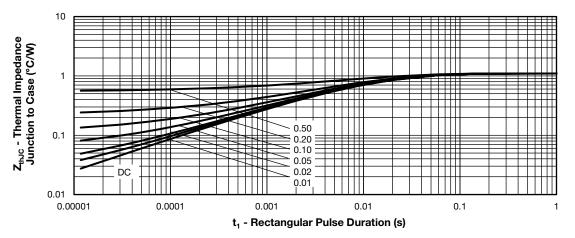


Fig. 6 - Thermal Impedance Z_{thJC} - Characteristics

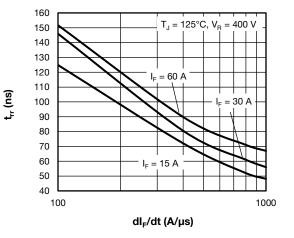
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Fig. 7 - Typical Reverse Recovery Time vs. dl_F/dt

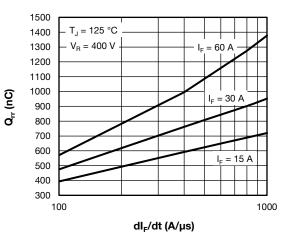


Fig. 8 - Typical Reverse Recovery Charge vs. dl_F/dt

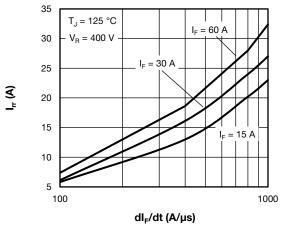


Fig. 9 - Typical Reverse Recovery Current vs. dl_F/dt

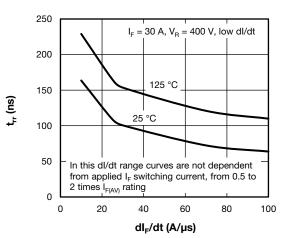
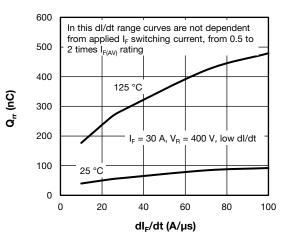


Fig. 10 - Typical Reverse Recovery Time vs. dl_F/dt





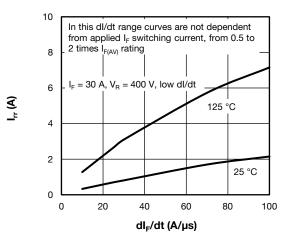


Fig. 12 - Typical Reverse Recovery Current vs. dl_F/dt

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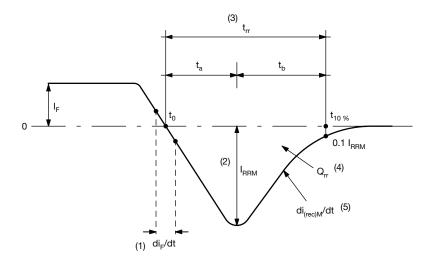


Fig. 13 - Reverse Recovery Waveform and Definitions

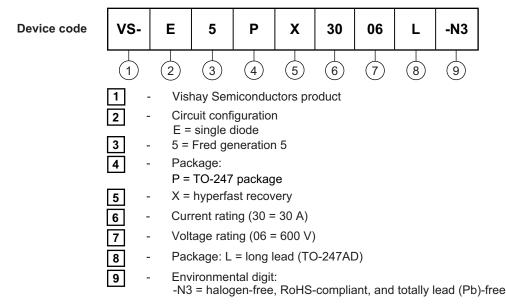
Notes

- $^{(1)}$ di_F/dt rate of change of current through zero crossing
- (2) I_{RRM} peak reverse recovery current (3) t_{rr} reverse recovery time measured from t_0 , crossing point of negative going I_F , to point $t_{10\%}$, 0.1 I_{RRM} (4) Q_{rr} area under curve defined by t_0 and $t_{10\%}$

$$Q_{rr} = \int_{t_0}^{t_{10\%}} I(t) dt$$

 $^{(5)}$ di_(rec)M/dt - peak rate of change of current during t_b portion of t_{rr}

ORDERING INFORMATION TABLE



ORDERING INFORMATION (Example)								
PREFERRED P/N	QUANTITY PER TUBE	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION					
VS-E5PX3006L-N3	25	500	Antistatic plastic tube					
LINKS TO RELATED DOCUMENTS								
Dimensions	Dimensions www.vishay.com/doc?95536							
Part marking information	mation www.vishay.com/doc?95648							
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